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NORME INTERNATIONALE

Semiconductor devices – Mechanical and climatic test methods – Part 44: Neutron beam irradiated single event effect (SEE) test method for semiconductor devices

Dispositifs à semiconducteurs – Méthodes d'essais mécaniques et climatiques – Partie 44: Méthode d'essai des effets d'un événement isolé (SEE) irradié par un faisceau de neutrons pour des dispositifs à semiconducteurs

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IEC Central Office
3, rue de Varembé
CH-1211 Geneva 20
Switzerland

Tel.: +41 22 919 02 11
Fax: +41 22 919 03 00
info@iec.ch
www.iec.ch

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CONTENTS

FOREWORD....4
1 Scope....6
2 Normative references....6
3 Terms and definitions....6
4 Test apparatus....9
4.1 Measurement equipment....9
4.2 Radiation source....10
4.3 Test sample....10
5 Procedure neutron irradiated soft error test....10
5.1 Surface preparation....10
5.2 Power supply voltage....10
5.3 Ambient temperature....11
5.4 Core cycle time....11
5.5 Data pattern....11
5.6 Number of measurement samples....11
5.7 Calculations for time required in the beam....11
6 Evaluation....11
6.1 Measurement and failure rate estimation....11
6.2 Determination of MCU and MBU cross sections....12
6.3 Determination of device FIT (event rate) from cross section....12
7 Summary....12
Annex A (informative) Additional information for the applicable procurement specification....13
A.1 General....13
A.2 Description of the beam source....13
A.3 Description of the sample and test vehicle....13
A.3.1 Sample size....13
A.3.2 Vehicle description....13
A.4 Test description....14
A.5 Test results....14
Annex B (informative) White neutron test apparatus....16
Annex C (informative) Failure rate calculation....18
C.1 An influence of soft error for actual semiconductor devices....18
C.1.1 General....18
C.1.2 Duty derating....18
C.1.3 Utility derating....18
C.1.4 Critically derating....19
C.2 Failure rate calculation including derating....19
Bibliography....20

Figure B.1 – Typical white neutron spectra with different shield (polyethylene) thickness....16
Figure B.2 – Typical neutron spectrum....17
Figure B.3 – Comparison of LANSCE (WNR) and TRIUMF neutron spectra with terrestrial neutron spectrum....17

Figure C.1 – Schematic image of duty derating 18
Figure C.2 – Schematic image of memory effective area for utility derating 19

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SEMICONDUCTOR DEVICES – MECHANICAL AND CLIMATIC TEST METHODS –

Part 44: Neutron beam irradiated single event effect (SEE) test method for semiconductor devices

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The text of this standard is based on the following documents:

FDIS	Report on voting
47/2303/FDIS	47/2312/RVD

Full information on the voting for the approval of this standard can be found in the report on voting indicated in the above table.

This publication has been drafted in accordance with the ISO/IEC Directives, Part 2.

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SEMICONDUCTOR DEVICES – MECHANICAL AND CLIMATIC TEST METHODS –

Part 44: Neutron beam irradiated single event effect (SEE) test method for semiconductor devices

1 Scope

This part of IEC 60749 establishes a procedure for measuring the single event effects (SEEs) on high density integrated circuit semiconductor devices including data retention capability of semiconductor devices with memory when subjected to atmospheric neutron radiation produced by cosmic rays. The single event effects sensitivity is measured while the device is irradiated in a neutron beam of known flux. This test method can be applied to any type of integrated circuit.

NOTE 1 Semiconductor devices under high voltage stress can be subject to single event effects including SEB, single event burnout and SEGR single event gate rupture, for this subject which is not covered in this document, please refer to IEC 62396-4 [2].

NOTE 2 In addition to the high energy neutrons some devices can have a soft error rate due to low energy (<1 eV) thermal neutrons. For this subject which is not covered in this document, please refer to IEC 62396-5 [3].

2 Normative references

The following documents, in whole or in part, are normatively referenced in this document and are indispensable for its application. For dated references, only the edition cited applies. For undated references, the latest edition of the referenced document (including any amendments) applies.

None.

3 Terms and definitions

For the purposes of this document, the following terms and definitions apply.

3.1
critical charge
Qcrit
smallest charge that will cause a SEE if injected or deposited in the sensitive volume

3.2
single-event upset
SEU
in a semiconductor device when the radiation absorbed by the device is sufficient to change a cell’s logic state

Note 1 to entry: After a new write cycle, the original state can be recovered.

3.3
multiple bit upset
MBU
energy deposited in the silicon of an electronic component by a single ionising particle causing more than one bit in the same word to be upset

Note 1 to entry: The definition of MBU has been updated due to the introduction of the definition of MCU.